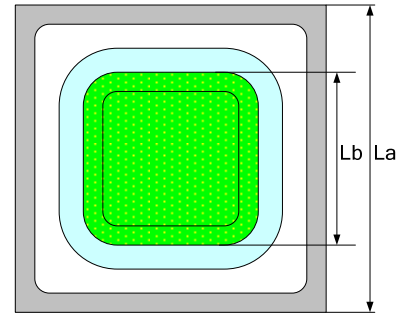


2ES032XXXJL SERIES TRANSIENT VOLTAGE SUPPRESSORS

DESCRIPTION

- 2ES032XXXJL series are transient voltage suppressors diode chips for plastic package that fabricated in silicon epitaxial planar technology;
- Excellent clamping capability;
- Fast response time ;
- Low leakage;
- ESD>16KV(Human Body Model);
- Top metal is AL, Back metal is Au;
- Chip size: 320μm X 320μm;
- Chip Thickness: 180±20μm.



2ES032XXX JLCHIP TOPOGRAPHY

La: Chip Size: 320μm;

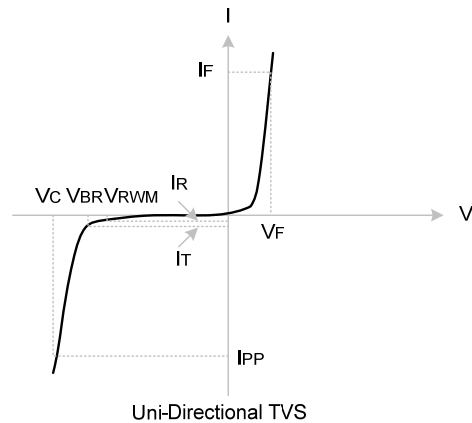
Lb: Pad Size: 180μm;

ABSOLUTE MAXIMUM RATINGS

Characteristics	Symbol	Value	Unit
Total Power Dissipation@ Tamb=25°C	PD	200	mW
Maximum Operation Junction Temperature	TJ	175	°C
Storage Temperature Range	Tstg	-50~+175	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C)

Symbol	Parameters
IPP	Maximum reverse peak pulse current
VC	Clamping voltage @ IPP
VRWM	Working peak reverse voltage
IR	Maximum reverse leakage current @ VRWM
VBR	Breakdown voltage @ IT
IT	Test current



ELECTRICAL CHARACTERISTICS (For packaged diodes, T_{amb}=25°C)

Type	V _{RWM} (V)	I _R (μA)@ V _{RWM}	V _{BR} (V) @I _T	I _T	V _C (V)@ Max I _{PP}	I _{PP} (A)*	P _{PK} (W)	C(PF)
	Max.	Max.	Typ.	mA	Max.	Max	Max	Typ.
2ES032025JL	2.5	6.0	4.0	1.0	10.9	11.0	120	145
2ES032033JL	3.3	0.05	5.0	1.0	14.1	11.2	158	105
2ES032050JL	5.0	0.05	6.2	1.0	18.6	9.4	174	80
2ES032060JL	6.0	0.01	6.8	1.0	20.5	8.8	181	70
2ES032070JL	7.0	0.01	7.5	1.0	22.7	8.8	200	65
2ES032120JL	12.0	0.01	14.1	1.0	25.0	9.6	240	55

Note: 1. V_F<0.9V@I_F=10mA for all types;
2. * 8×20μm plus waveform.